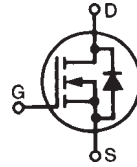
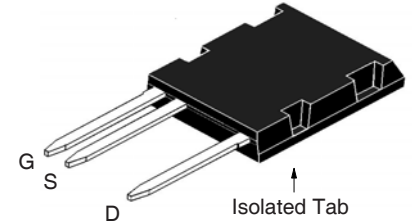


**Polar™ HiPerFET™
Power MOSFET**
IXFL36N110P
(Electrically Isolated Tab)

 N-Channel Enhancement Mode
 Avalanche Rated
 Fast Intrinsic Rectifier

$$\begin{aligned} V_{DSS} &= 1100V \\ I_{D25} &= 26A \\ R_{DS(on)} &\leq 260m\Omega \\ t_{rr} &\leq 300ns \end{aligned}$$

ISOPLUS i5-Pak™

 G = Gate
 D = Drain

S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1100	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	1100	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	26	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	110	A
I_A	$T_C = 25^\circ\text{C}$	18	A
E_{AS}	$T_C = 25^\circ\text{C}$	2	J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	20	V/ns
P_D	$T_C = 25^\circ\text{C}$	520	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10s	260	$^\circ\text{C}$
F_C	Mounting Force	20..120 / 4.5..27	N/lb.
V_{ISOL}	50/60 Hz, RMS $t = 1$ min	2500	V~
	$I_{ISOL} \leq 1$ mA $t = 1$ s	3000	V~
Weight		8	g

Features

- Silicon Chip on Direct-Copper-Bond Substrate
 - High Power Dissipation
 - Isolated Mounting Surface
 - 2500V~ Electrical Isolation
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- Low $R_{DS(on)}$ and Q_G

Advantages

- Easy to Mount
- Space Savings

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- AC Motor Control
- High Speed Power Switching Application

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 3mA$	1100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1mA$	3.5		V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 300 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			50 μA 4 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 18A$, Note 1			260 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}, I_D = 18\text{A}$, Note 1	20	32	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		23	nF
			1240	pF
			110	pF
R_{Gi}	Gate Input Resistance		0.85	Ω
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 18\text{A}$ $R_G = 1\Omega$ (External)		60	ns
			54	ns
			94	ns
			45	ns
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 18\text{A}$		350	nC
			117	nC
			157	nC
R_{thJC} R_{thCS}		0.15		0.24°C/W $^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			36 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			144 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr} Q_{RM} I_{RM}	$I_F = 20\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
			2.3	μC
			16.0	A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

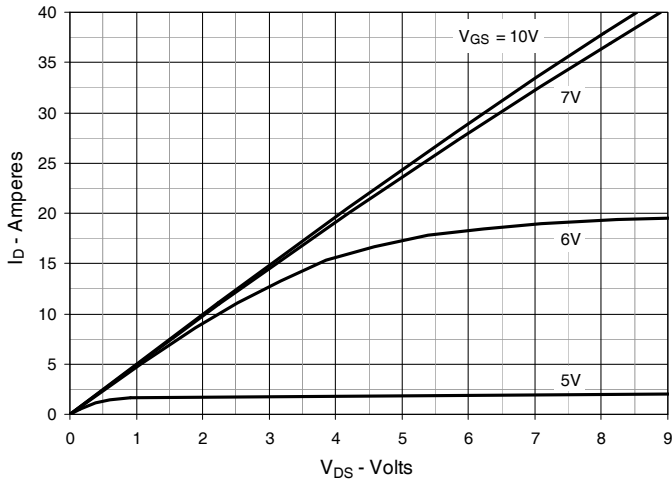


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

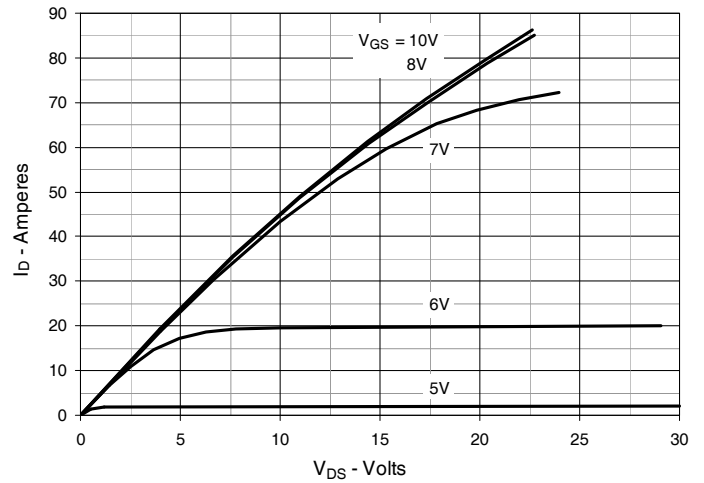


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

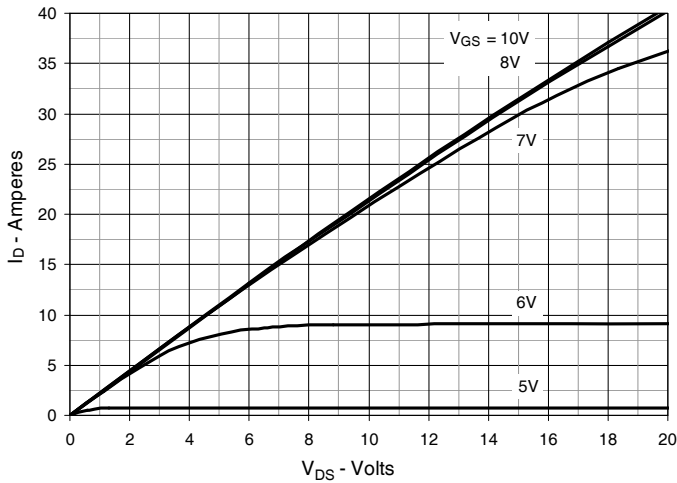


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 18\text{A}$ Value vs. Junction Temperature

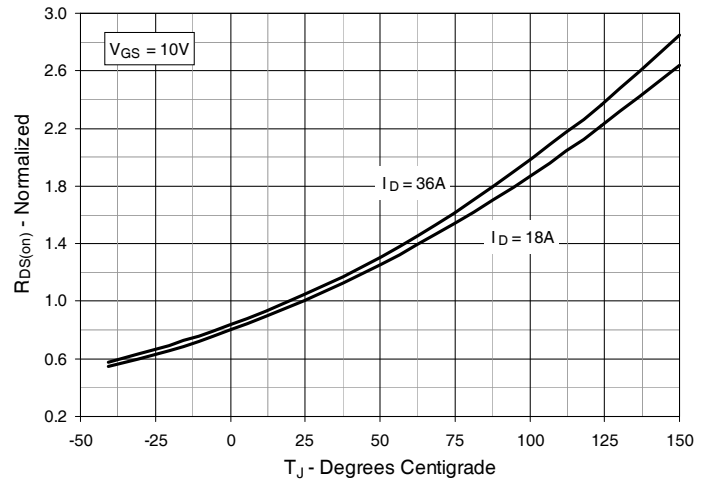


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 18\text{A}$ Value vs. Drain Current

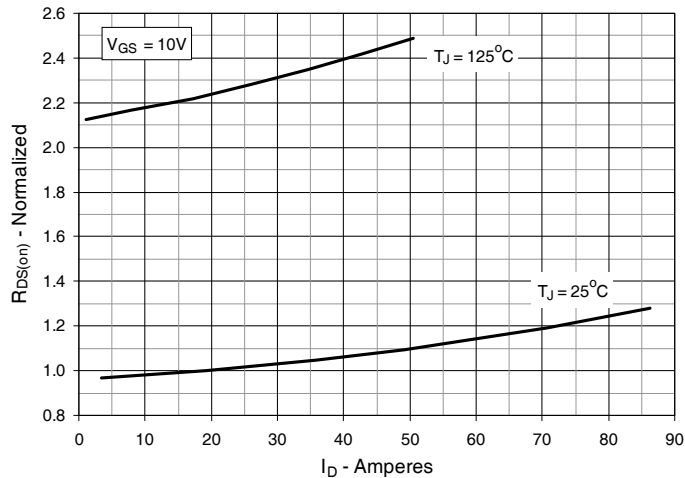


Fig. 6. Maximum Drain Current vs. Case Temperature

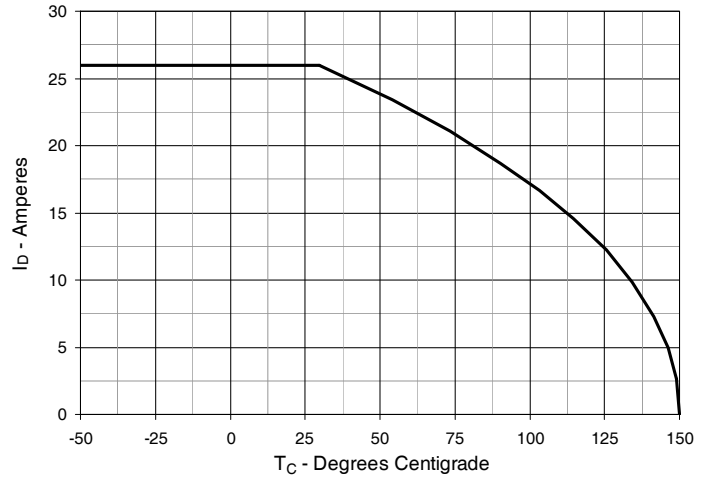


Fig. 7. Input Admittance

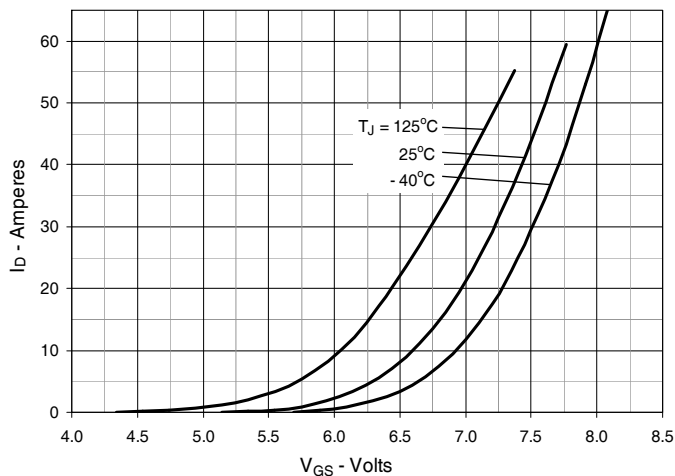


Fig. 8. Transconductance

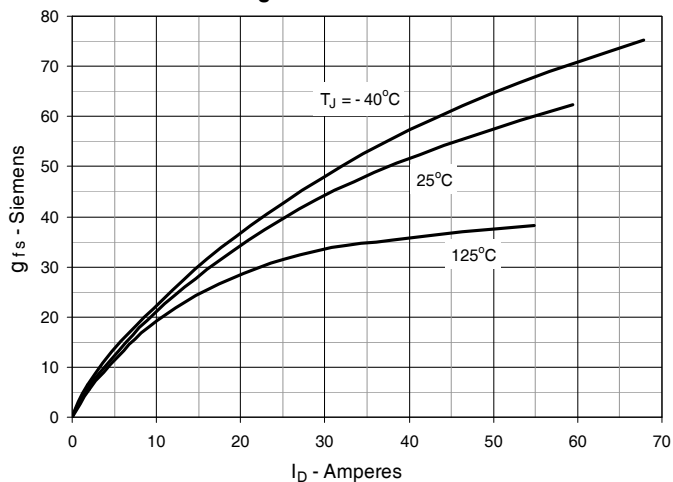


Fig. 9. Forward Voltage Drop of Intrinsic Diode

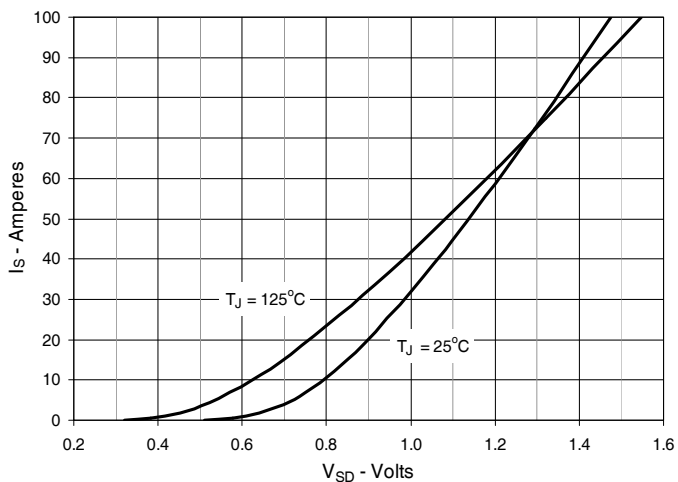


Fig. 10. Gate Charge

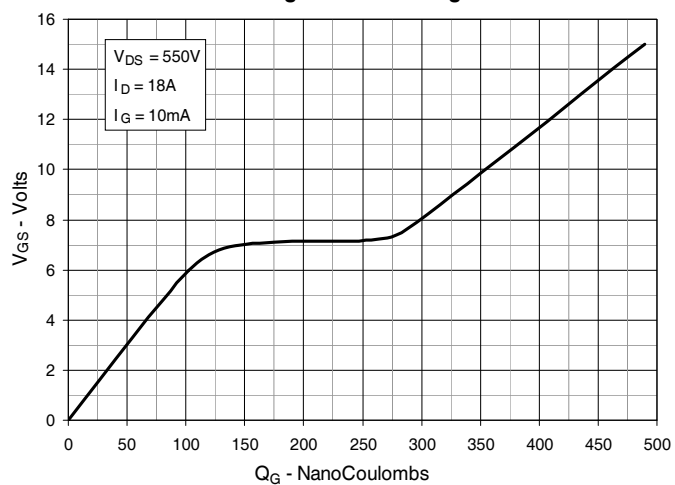


Fig. 11. Capacitance

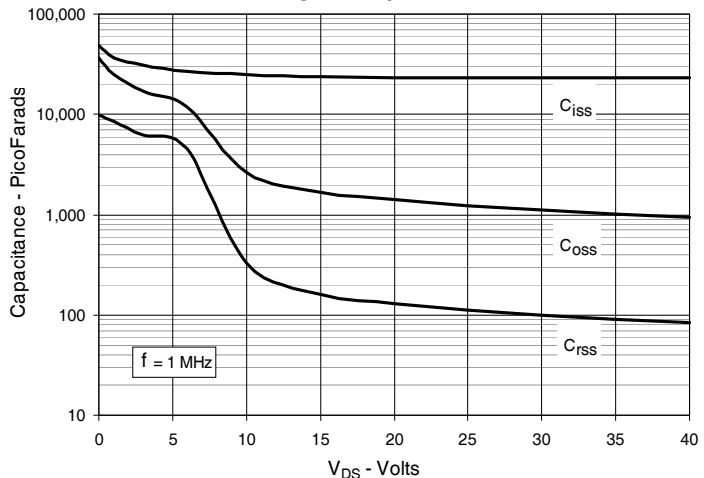
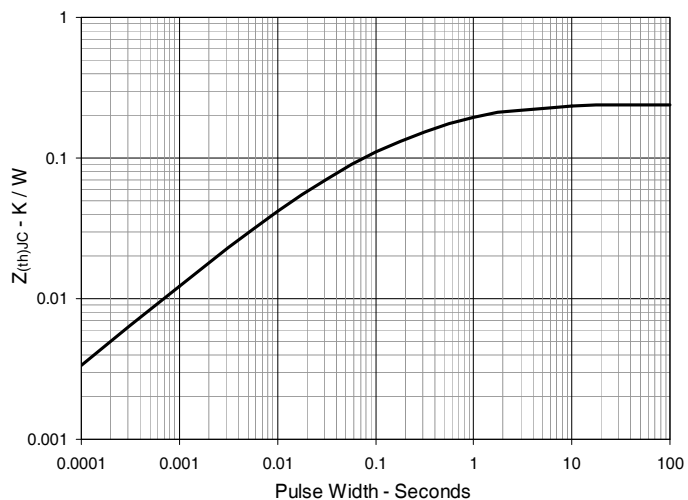
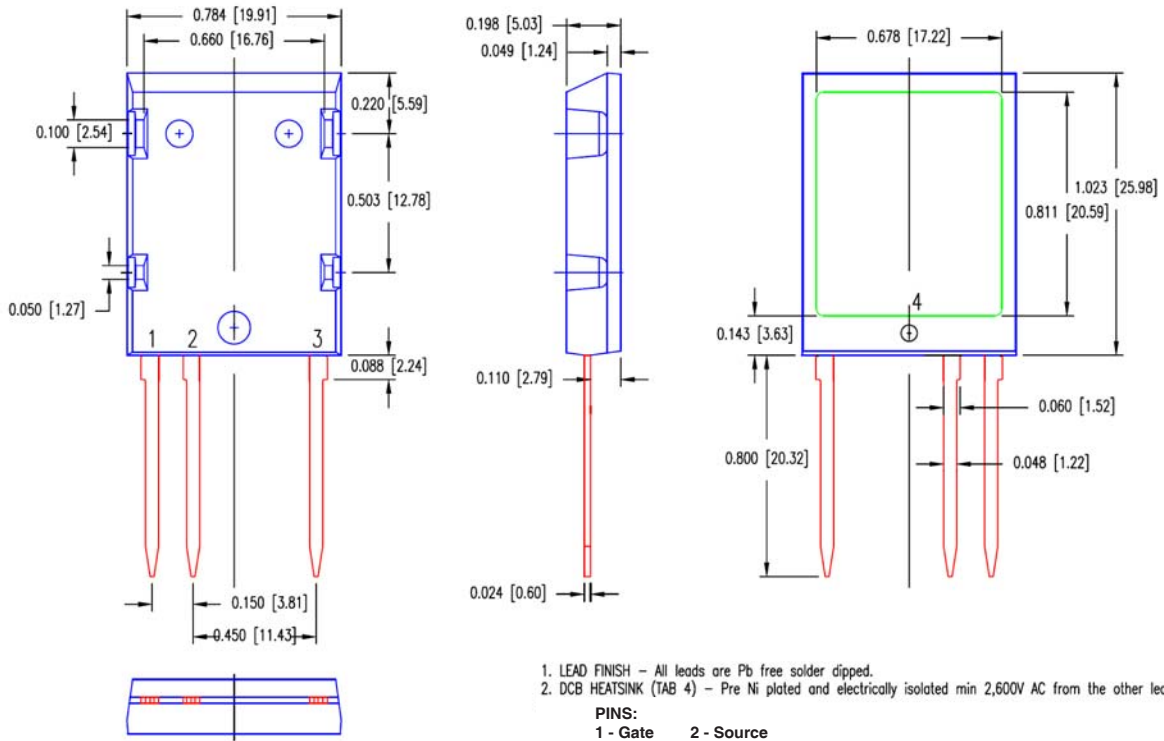


Fig. 12. Maximum Transient Thermal Impedance



ISOPLUS i5-Pak™ (IXFL) Outline




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